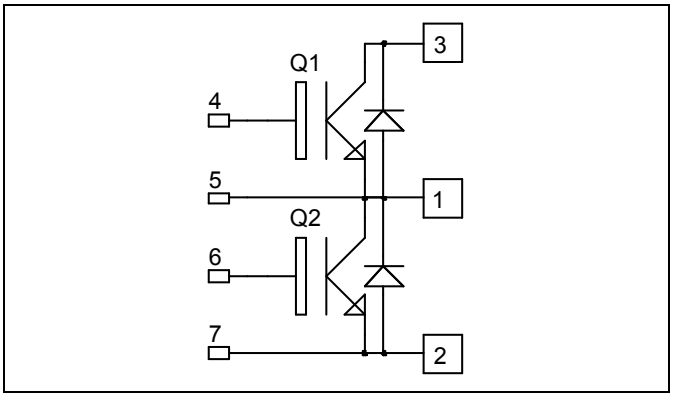
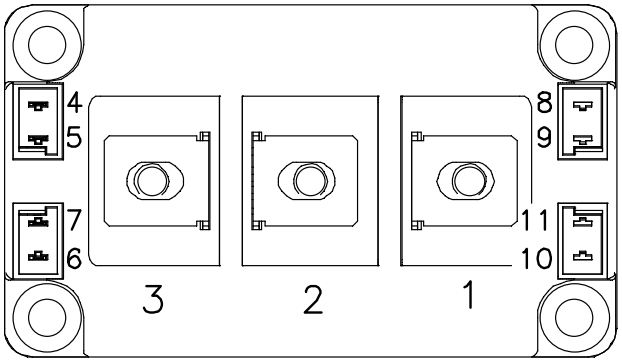
Phase leg NPT IGBT Power Module

V_{CES} = 600V
I_C = 250A @ Tc = 80°C





Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Non Punch Through (NPT) FAST IGBT
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 50 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- High level of integration
- M6 power connectors

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CEsat}
- RoHS Compliant

Absolute maximum ratings

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{CES}	Collector - Emitter Breakdown Voltage		600	V
I_C	Continuous Collector Current	T_C = 25°C	400	A
		T_C = 80°C	250	
I_{CM}	Pulsed Collector Current	T_C = 25°C	600	
V_{GE}	Gate – Emitter Voltage		±20	V
P_D	Maximum Power Dissipation	T_C = 25°C	1250	W
RBSOA	Reverse Bias Safe Operating Area	T_j = 125°C	600A @ 520V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.
See application note APT0502 on www.microsemi.com

All ratings @ T_j = 25°C unless otherwise specified

Electrical Characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
I_{CES}	Zero Gate Voltage Collector Current	V_{GE} = 0V, V_{CE} = 600V				500	µA
$V_{CE(sat)}$	Collector Emitter saturation Voltage	V_{GE} = 15V, I_C = 300A	T_j = 25°C		1.95	2.45	V
			T_j = 125°C		2.2		
$V_{GE(th)}$	Gate Threshold Voltage	V_{GE} = V_{CE} , I_C = 6 mA		5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	V_{GE} = 20V, V_{CE} = 0V				400	nA

Dynamic Characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
C_{ies}	Input Capacitance	V_{GE} = 0V ; V_{CE} = 25V f = 1MHz			13		nF
C_{res}	Reverse Transfer Capacitance				1.2		
Q_G	Gate charge	V_{GE}=15V, I_C=300A V_{CE}=300V			720		nC
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) V_{GE} = ±15V V_{Bus} = 300V I_C = 300A R_G = 6Ω			150		ns
T_r	Rise Time				72		
$T_{d(off)}$	Turn-off Delay Time				530		
T_f	Fall Time				40		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) V_{GE} = ±15V V_{Bus} = 300V I_C = 300A R_G = 6Ω			160		ns
T_r	Rise Time				75		
$T_{d(off)}$	Turn-off Delay Time				550		
T_f	Fall Time				50		
E_{on}	Turn on Energy	V_{GE} = ±15V V_{Bus} = 300V I_C = 300A R_G = 6Ω	T_j = 125°C		14		mJ
E_{off}	Turn off Energy		T_j = 125°C		13		
I_{sc}	Short Circuit data	V_{GE} ≤15V ; V_{Bus} = 360V t_p ≤ 10µs ; T_j = 125°C			1350		A

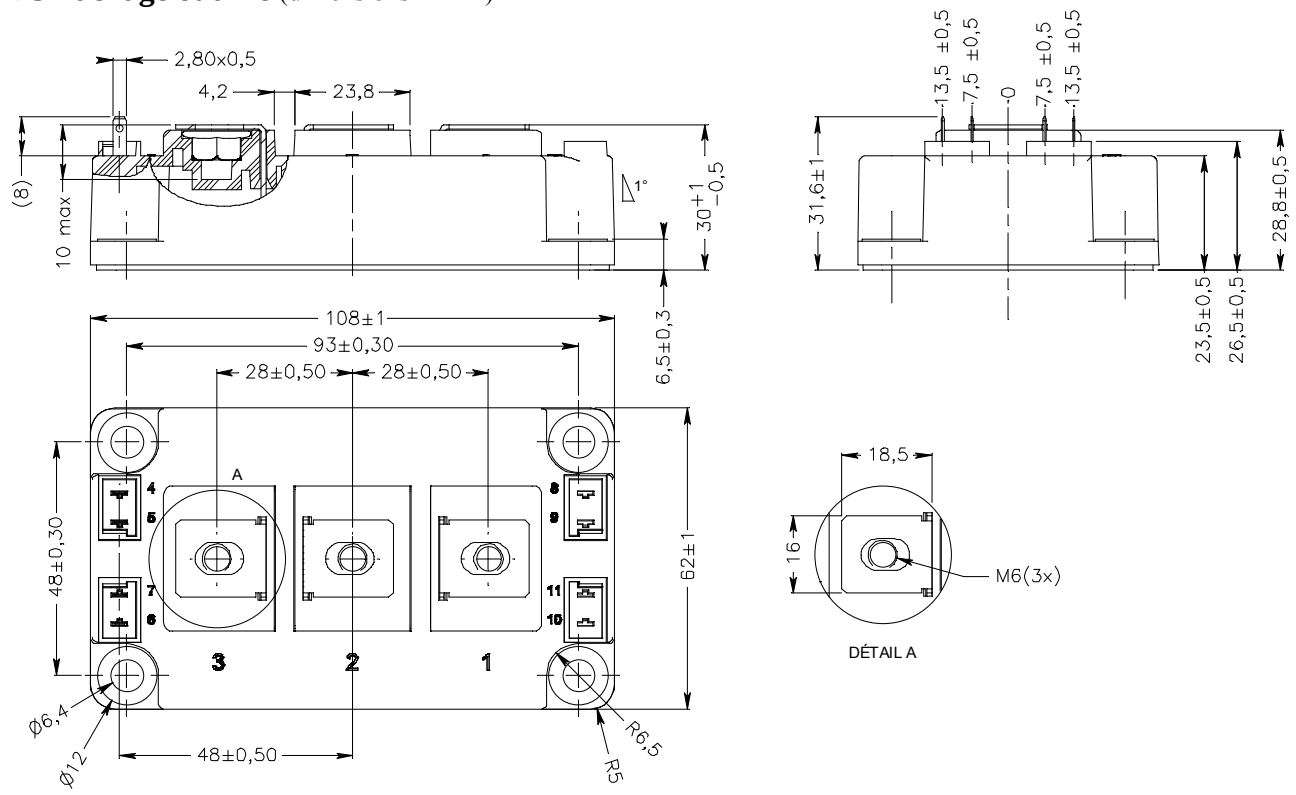
Reverse diode ratings and characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I_{RRM}	Maximum Reverse Leakage Current	V_R=600V	T_j = 25°C			750	µA
			T_j = 125°C			1000	
I_F	DC Forward Current		Tc = 80°C		300		A
V_F	Diode Forward Voltage	I_F = 300A V_{GE} = 0V	T_j = 25°C		1.25	1.6	V
			T_j = 125°C		1.2		
t_{rr}	Reverse Recovery Time	I_F = 300A V_R = 300V di/dt =4800A/µs	T_j = 25°C		150		ns
			T_j = 125°C		250		
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		20		µC
			T_j = 125°C		32		
E_{rr}	Reverse Recovery Energy		T_j = 25°C		4		mJ
			T_j = 125°C		7.6		

Thermal and package characteristics

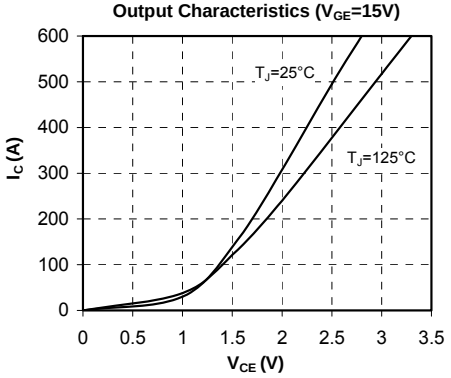
Symbol	Characteristic			Min	Typ	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance		IGBT			0.1	°C/W
			Diode			0.21	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz			2500			V
T_J	Operating junction temperature range			-40		150	°C
T_{STG}	Storage Temperature Range			-40		125	
T_C	Operating Case Temperature			-40		125	
Torque	Mounting torque	For terminals	M6	3		5	N.m
		To Heatsink	M6	3		5	
Wt	Package Weight					350	g

D3 Package outline (dimensions in mm)

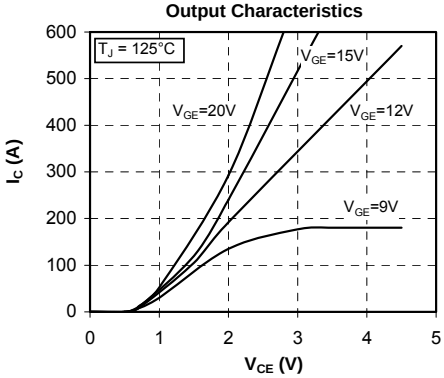


Typical Performance Curve

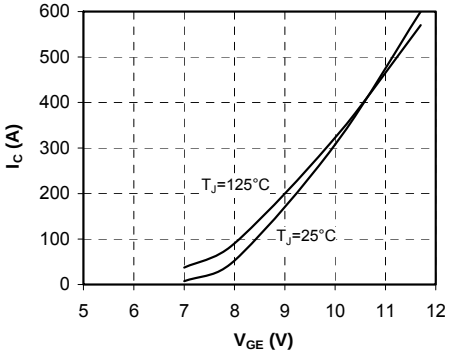
Output Characteristics (V_{GE}=15V)



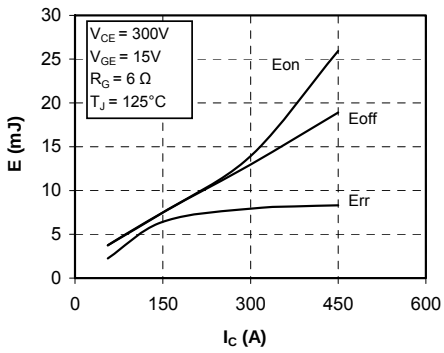
Output Characteristics



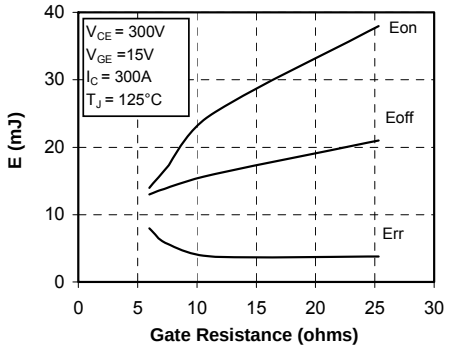
Transfert Characteristics



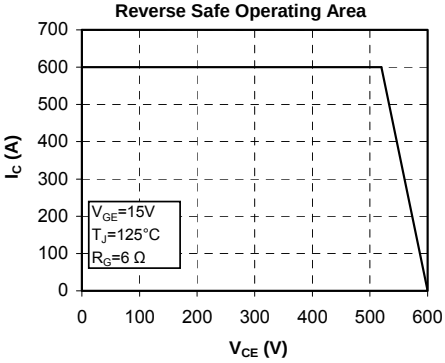
Energy losses vs Collector Current



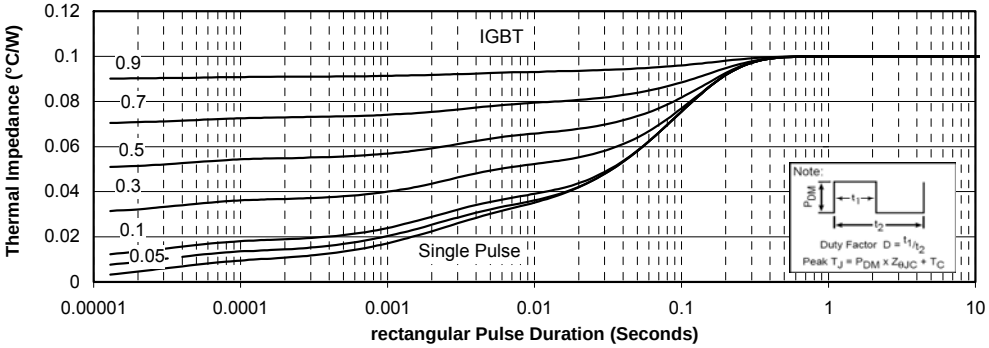
Switching Energy Losses vs Gate Resistance

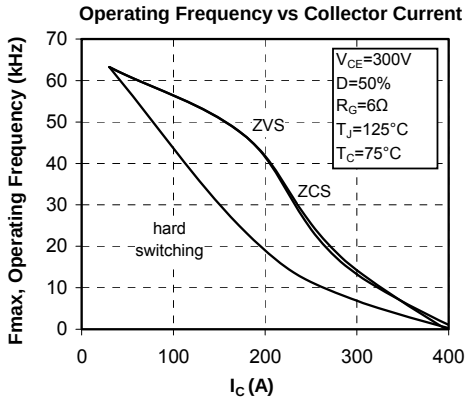


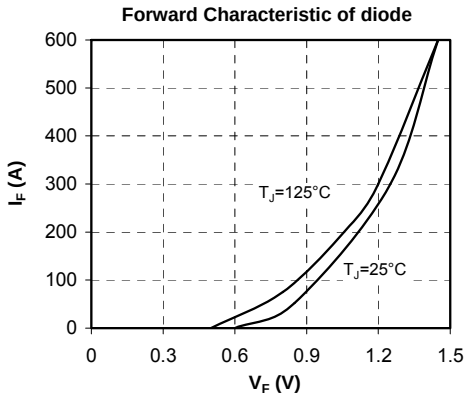
Reverse Safe Operating Area

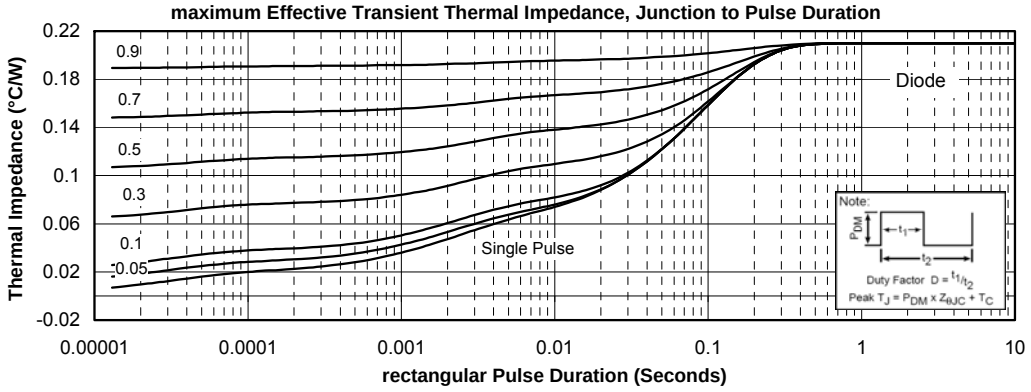


maximum Effective Transient Thermal Impedance, Junction to Pulse Duration









Microsemi reserves the right to change, without notice, the specifications and information contained herein

Microsemi's products are covered by one or more of U.S patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 6,939,743 7,352,045 5,283,201 5,801,417 5,648,283 7,196,634 6,664,594 7,157,886 6,939,743 7,342,262 and foreign patents. U.S and Foreign patents pending. All Rights Reserved.